MOTOROLA8供应商 SEMICONDUCTOR TECHNICAL DATA

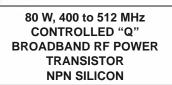
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by MRF338/D

The RF Line **NPN Silicon RF Power Transistor**

Designed primarily for wideband large-signal output and driver amplifier stages in the 400 to 512 MHz frequency range.

- Specified 28 Volt, 470 MHz Characteristics Output Power = 80 Watts Minimum Gain = 7.3 dB Efficiency = 50% (Min)
- Built–In Matching Network for Broadband Operation
- 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR
- Gold Metallization System for High Reliability Applications •



MRF338



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	VCBO	60	Vdc
Emitter-Base Voltage	VEBO	4	Vdc
Collector Current — Continuous — Peak	^I C	9 12	Adc
Total Device Dissipation @ T _C = 25°C (1) Derate above 25°C	PD	250 1.43	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	R _{0JC}	0.7	°C/W
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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 80 \text{ mAdc}, I_B = 0$)	V(BR)CEO	30	_	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 80 \text{ mAdc}, V_{BE} = 0$)	V _(BR) CES	60	_	—	Vdc
Emitter–Base Breakdown Voltage (I _E = 8 mAdc, I _C = 0)	V(BR)EBO	4	_	_	Vdc

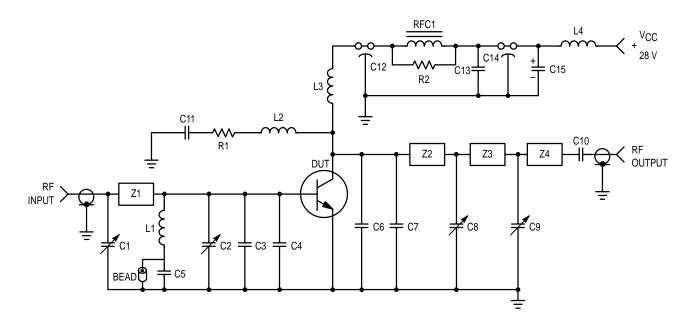
(1) This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier. (2) Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.





Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			-	-	
Collector–Base Breakdown Voltage $(I_{C} = 80 \text{ mAdc}, I_{E} = 0)$	V(BR)CBO	60	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 30 Vdc, I_E = 0$)	ІСВО	_	-	5	mAdc
ON CHARACTERISTICS	•		•		•
DC Current Gain (I _C = 4 Adc, V _{CE} = 5 Vdc)	hFE	20	-	80	-
DYNAMIC CHARACTERISTICS	•		•		•
Output Capacitance ($V_{CB} = 28 \text{ Vdc}, I_E = 0, f = 1 \text{ MHz}$)	C _{ob}	_	95	125	pF
FUNCTIONAL TESTS (Figure 1)			•		
Common–Emitter Amplifier Power Gain (V _{CC} = 28 Vdc, P _{out} = 80 W, f = 470 MHz)	GPE	7.3	8.8	-	dB
Collector Efficiency (V _{CC} = 28 Vdc, P _{OUt} = 80 W, f = 470 MHz)	η	50	60	-	%
Load Mismatch (V _{CC} = 28 Vdc, P _{out} = 80 W, f = 470 MHz, VSWR = 30:1, All Phase Angles at Frequency of Test)	Ψ	No Degradation in Output Power			

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^{\circ}C$ unless otherwise noted)



Bead	Ferroxcube #56–590–65/3B	L3	3 Turns #18 AWG, 0.185" ID, Close Wound
C1, C2, C8, C9	0.8–20 pF, Johanson (JMC 5501)	L4	4 Turns #18 AWG, 0.185" ID, Close Wound
C3, C4, C6, C7	25 pF, 100 V, Underwood	RFC1	Ferroxcube VK200 19/4B
C5, C10	100 pF, 100 V, Underwood	R1, R2	10 Ω, 2.0 Watt Carbon
C11, C13	0.1 μF, Erie Redcap	Z1	0.190" W x 2.5" L, Microstrip Lin
C12, C14	680 pF, Feedthru	Z2	0.190" W x 0.289" L, Microstrip Line
C15	1.0 μF, Tantalum	Z3	0.190" W x 0.55" L, Microstrip Line
L1	0.15 μH, Molded Choke	Z4	0.190" W x 0.325" L, Microstrip Line
L2	5 Turns #20 AWG, 0.185" ID, Close Wound	Board	Glass Teflon, t = 0.062", ϵ_r = 2.56

TYPICAL CHARACTERISTICS

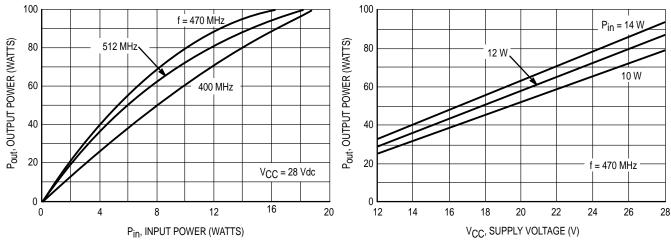




Figure 3. Output Power versus Supply Voltage

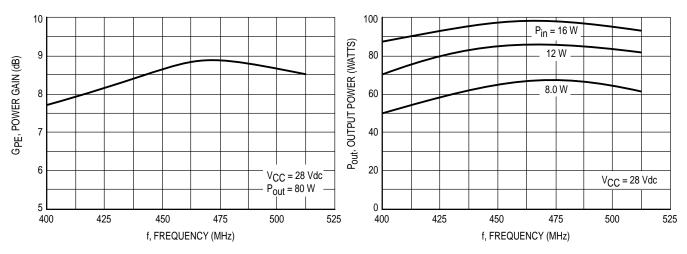
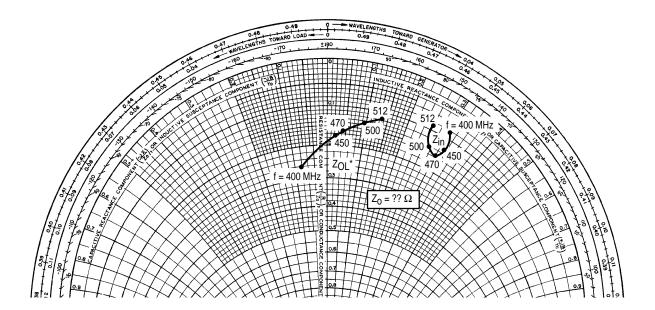


Figure 4. Power Gain versus Frequency

Figure 5. Output Power versus Frequency

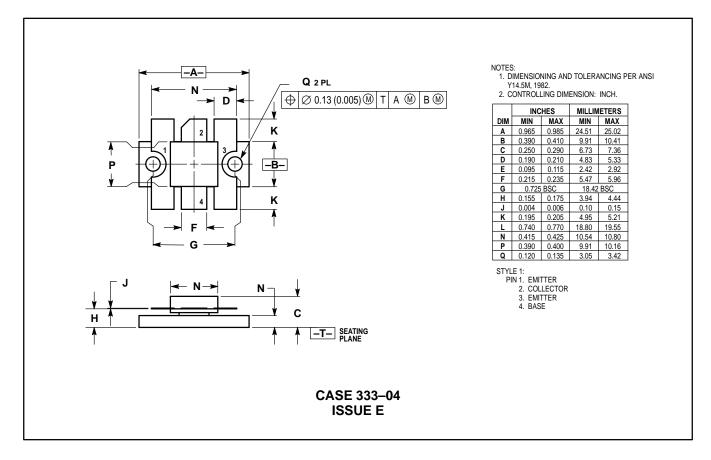


V _{CC} = 28 V, P _{out} = 80 W			
f	Z _{in}	Z _{OL} *	
MHz	Ohms	Ohms	
512	0.91 + j2.61	1.19 + j1.34	
500	1.47 + j2.71	1.33 + j0.96	
470	1.53 + j2.98	1.60 + j0.45	
450	1.27 + j3.09	1.70 + j0.25	
400	0.86 + j3.01	2.58 – j0.79	

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.



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JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 4-32-1,

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298